

ABSTRACT OF THE INVENTION

A nonvolatile memory cell having a floating gate for the storage of charges thereon has a control gate and a separate erase gate. The cell is programmed by hot channel electron injection and is erased by poly to poly Fowler-Nordheim tunneling. A method for making an array of 5 unidirectional cells in a planar substrate, as well as an array of bidirectional cells in a substrate having a trench, is disclosed. An array of such cells and a method of making such an array is also disclosed.